

CMOS BCD-to-7-Segment Latch Decoder Drivers

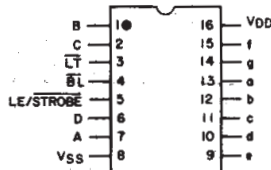
High-Voltage Types (20-Volt Rating)



■ CD4511B types are BCD-to-7-segment latch decoder drivers constructed with CMOS logic and n-p-n bipolar transistor output devices on a single monolithic structure. These devices combine the low quiescent power dissipation and high noise immunity features of RCA CMOS with n-p-n bipolar output transistors capable of sourcing up to 25 mA. This capability allows the CD4511B types to drive LED's and other displays directly.

Lamp Test (LT), Blanking (BL), and Latch Enable or Strobe inputs are provided to test the display, shut off or intensity-modulate it, and store or strobe a BCD code, respectively. Several different signals may be multiplexed and displayed when external multiplexing circuitry is used. The CD4511B is supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

These devices are similar to the type MC14511.



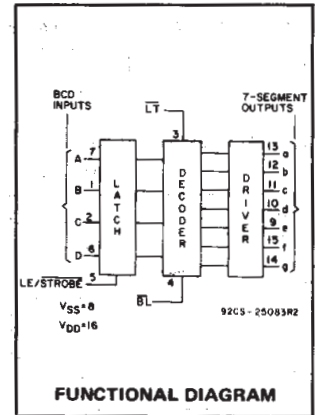
TOP VIEW
92CS-25084RI
CD4511B
TERMINAL ASSIGNMENT

Features:

- High-output-sourcing capability up to 25 mA
- Input latches for BCD Code storage
- Lamp Test and Blanking capability
- 7-segment outputs blanked for BCD input codes > 1001
- 100% tested for quiescent current at 20 V
- Max. input current of 1 μ A at 18 V, over full package-temperature range, 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings

Applications:

- Driving common-cathode LED displays
- Multiplexing with common-cathode LED displays
- Driving incandescent displays
- Driving low-voltage fluorescent displays



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V _{DD})	-0.5V to +20V
Voltages referenced to V _{SS} Terminal	
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to V _{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT	±10mA
POWER DISSIPATION, PER PACKAGE (P _D):	
For T _A = -55°C to +100°C	500mW
For T _A = +100°C to +125°C	Derate Linearly at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR T _A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100mW
OPERATING-TEMPERATURE RANGE (T _A)	-55°C to +125°C
STORAGE TEMPERATURE RANGE (T _{stg})	-65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max	+265°C

OPERATING CONDITIONS AT T_A = 25°C Unless Otherwise Specified

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges

Characteristic	V _{DD}	Min.	Max.	Units
Supply Voltage Range (T _A): (Full Package-Temperature Range)	-	3	18	V
Set-Up Time (t _S)	5	150	-	ns
	10	70	-	ns
	15	40	-	ns
Hold Time (t _H)	5	0	-	ns
	10	0	-	ns
	15	0	-	ns
Strobe Pulse Width (t _W)	5	400	-	ns
	10	160	-	ns
	15	100	-	ns

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

CD4511B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	TEST CONDITIONS				LIMITS AT INDICATED TEMPERATURES (°C)							Units	
	I _{OH} (mA)	V _o (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25				
									Min.	Typ.	Max.		
Quiescent Device Current: I _{DD} Max.	-	-	-	5	5	5	150	150	-	0.04	5	μA	
	-	-	-	10	10	10	300	300	-	0.04	10		
	-	-	-	15	20	20	600	600	-	0.04	20		
	-	-	-	20	100	100	3000	3000	-	0.08	100		
Output Voltage: Low-Level V _{OL} Max.	-	-	0.5	5	0.05				-	0	0.05	V	
	-	-	0.10	10	0.05				-	0	0.05		
	-	-	0.15	15	0.05				-	0	0.05		
High-Level V _{OH} Min.	-	-	0.5	5	4	4	4.2	4.2	4.1	4.55	-	V	
	-	-	0.10	10	9	9	9.2	9.2	9.1	9.55	-		
Input Low Voltage, V _{IL} Max.	-	0.5, 3.8	-	5	1.5				-	-	1.5	V	
	-	1.8, 8	-	10	3				-	-	3		
Input High Voltage, V _{IH} Min.	-	1.5, 13.8	-	15	4				-	-	4	V	
	-	0.5, 3.8	-	5	3.5				3.5	-	-		
	-	1.8, 8	-	10	7				7	-	-	V	
	-	1.5, 13.8	-	15	11				11	-	-		
Output Drive Voltage: High Level V _{OH} Min.	0	-	-	5	4.0	4.0	4.20	4.20	4.10	4.55	-	V	
	5	-	-		-	-	-	-	-	4.25	-		
	10	-	-		3.80	3.80	3.90	3.90	3.90	3.90	4.10		-
	15	-	-		-	-	3.50	3.50	-	-	3.95		-
	20	-	-		3.55	3.55	3.30	-	-	3.40	3.75		-
	25	-	-		3.40	3.40	-	-	-	3.10	3.55		-
	0	-	-	10	9.0	9.0	9.20	9.20	9.10	9.55	-	V	
	5	-	-		-	-	-	-	-	9.25	-		
	10	-	-		8.85	8.85	9.00	9.00	9.00	9.00	9.15		-
	15	-	-		-	-	-	-	-	-	9.05		-
	20	-	-		8.70	8.70	8.40	8.40	8.60	8.60	8.90		-
	25	-	-		8.60	8.60	-	-	8.30	8.30	8.75		-
0	-	-	15	14.0	14.0	14.20	14.20	14.10	14.55	-	V		
5	-	-		-	-	-	-	-	14.30	-			
10	-	-		13.90	13.90	14.0	14.0	14.0	14.0	14.20		-	
15	-	-		-	-	-	-	-	-	14.10		-	
20	-	-		13.75	13.75	13.50	13.50	13.70	13.70	13.95		-	
25	-	-		13.65	13.65	-	-	13.50	13.50	13.80		-	
Output Low (Sink) Current, I _{OL} Min.	-	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA	
	-	0.5	0.10	10	1.6	1.5	1.1	0.9	1.3	2.6	-		
	-	1.5	0.15	15	4.2	4	2.8	2.4	3.4	6.8	-		
Input Current, I _{IN} Max.	-	0.18	0.18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μA	

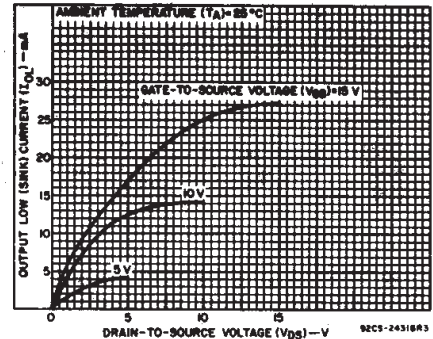


Fig. 1 - Typical output low (sink) current characteristics.

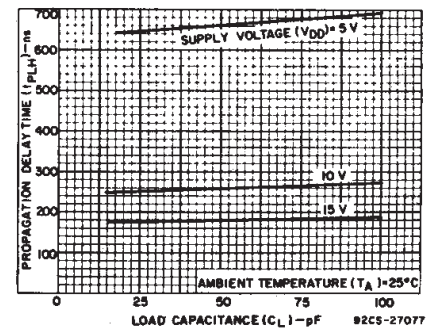


Fig. 2 - Typical data-to-output, low-to-high-level propagation delay time as a function of load capacitance.

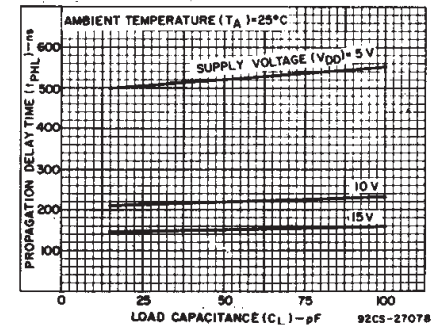


Fig. 3 - Typical data-to-output, high-to-low-level propagation delay time as a function of load capacitance.

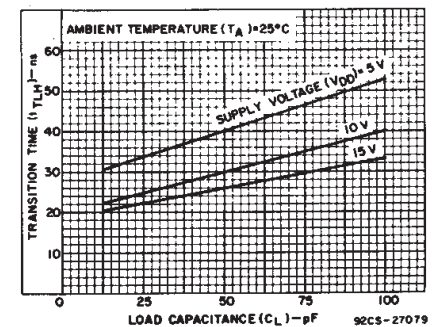


Fig. 4 - Typical low-to-high-level transition time as a function of load capacitance.

CD4511B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$, Input $t_r, t_f = 20\text{ ns}$,
 $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	Test Conditions	LIMITS All Packages			UNITS
		V_{DD} Volts	Min.	Typ.	
Propagation Delay Time: (Data) High-to-Low Level, t_{PHL}	5	—	520	1040	ns
	10	—	210	420	
	15	—	150	300	
Low-to-High Level, t_{PLH}	5	—	660	1320	ns
	10	—	260	520	
	15	—	180	360	
Propagation Delay Time: (BL) High-to-Low Level, t_{PHL}	5	—	350	700	ns
	10	—	175	350	
	15	—	125	250	
Low-to-High Level, t_{PLH}	5	—	400	800	ns
	10	—	175	350	
	15	—	150	300	
Propagation Delay Time: (LT) High-to-Low Level, t_{PHL}	5	—	250	500	ns
	10	—	125	250	
	15	—	85	170	
Low-to-High Level, t_{PLH}	5	—	150	300	ns
	10	—	75	150	
	15	—	50	100	
Transition Time: Low-to-High Level, t_{TLH}	5	—	40	80	ns
	10	—	30	60	
	15	—	25	50	
High-to-Low Level, t_{THL}	5	—	125	310	ns
	10	—	75	185	
	15	—	65	160	
Minimum Set-Up Time, t_S	5	150	75	—	ns
	10	70	35	—	
	15	40	20	—	
Minimum Hold Time, t_H	5	0	-75	—	ns
	10	0	-35	—	
	15	0	-20	—	
Strobe Pulse Width, t_W	5	400	200	—	ns
	10	160	80	—	
	15	100	50	—	
Input Capacitance, C_{IN}		—	5	7.5	pF

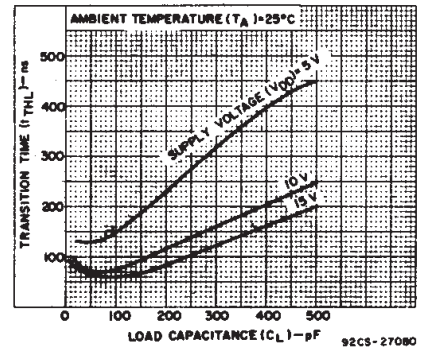


Fig. 5 - Typical high-to-low transition time as a function of load capacitance.

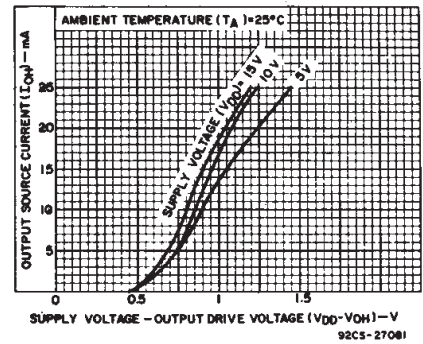


Fig. 6 - Typical voltage drop (V_{DD} to output) vs. output source current as a function of supply.

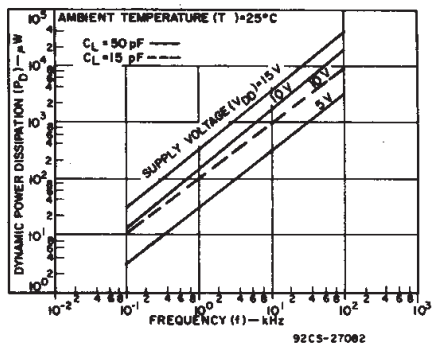


Fig. 7 - Typical dynamic power dissipation characteristics.

3
**COMMERCIAL CMOS
HIGH VOLTAGE ICs**

CD4511B Types

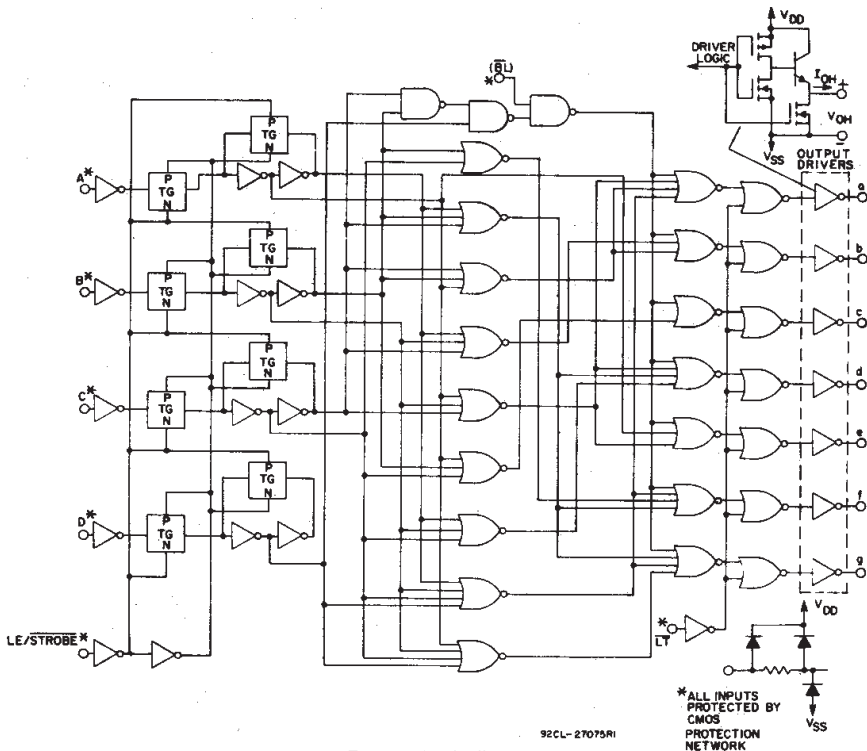


Fig. 8 - Logic diagram.

TRUTH TABLE

LE	BI	LT	D	C	B	A	a	b	c	d	e	f	g	Display
X	X	0	X	X	X	X	1	1	1	1	1	1	1	8
X	0	1	X	X	X	X	0	0	0	0	0	0	0	Blank
0	1	1	0	0	0	0	1	1	1	1	1	1	0	0
0	1	1	0	0	0	1	0	1	1	0	0	0	0	1
0	1	1	0	0	1	0	1	1	0	1	1	0	1	2
0	1	1	0	0	1	1	1	1	1	0	0	1	1	3
0	1	1	0	1	0	0	0	1	1	0	0	1	1	4
0	1	1	0	1	0	1	1	0	1	1	0	1	1	5
0	1	1	0	1	1	0	0	0	1	1	1	1	1	6
0	1	1	0	1	1	1	1	1	1	0	0	0	0	7
0	1	1	1	0	0	0	1	1	1	1	1	1	1	8
0	1	1	1	0	0	1	1	1	1	0	0	1	1	9
0	1	1	1	0	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	0	1	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	0	0	0	0	0	0	0	0	0	Blank
0	1	1	1	1	0	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	1	0	0	0	0	0	0	0	Blank
1	1	1	X	X	X	X	*	*	*	*	*	*	*	*

X = Don't Care * Depends on BCD code previously applied when LE = 0
 Note: Display is blank for all illegal input codes (BCD > 1001).

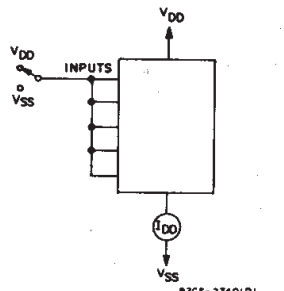


Fig. 9 - Quiescent device current.

TEST CIRCUITS

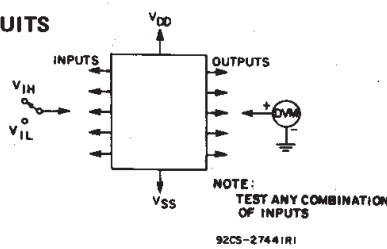


Fig. 10 - Input voltage.

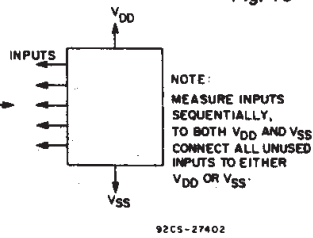


Fig. 11 - Input current.

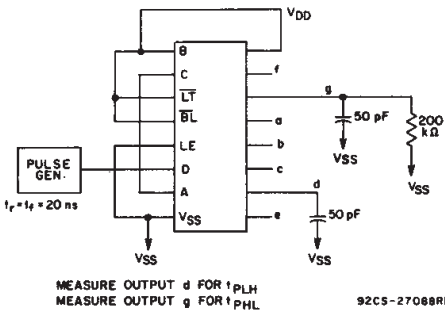


Fig. 12 - Data propagation delay.

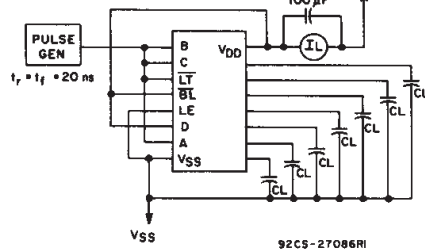
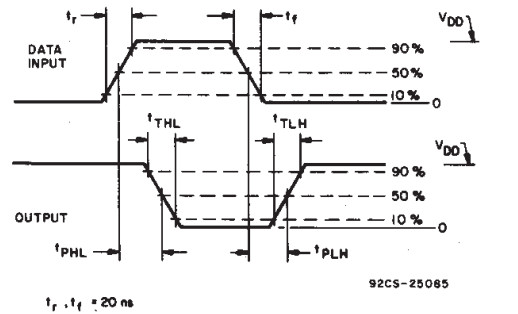


Fig. 13 - Dynamic power dissipation.



t_r, t_f = 20 ns

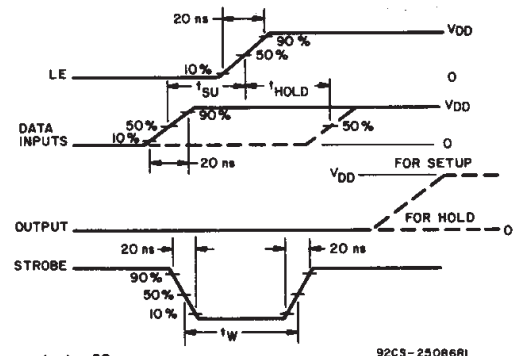
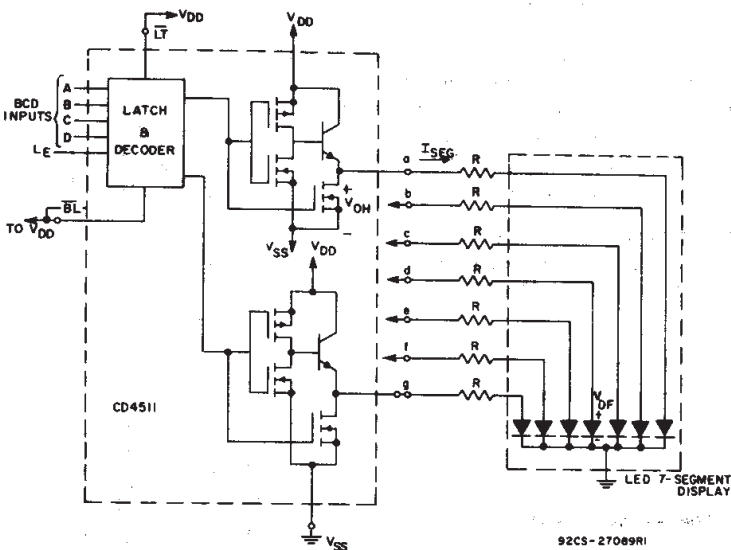


Fig. 14 - Dynamic waveforms.

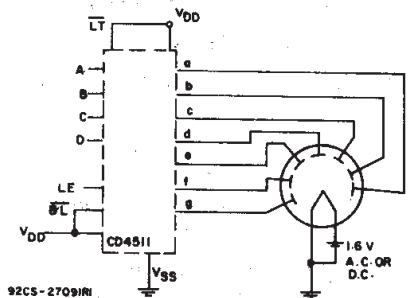
CD4511B Types

APPLICATIONS Interfacing with Various Displays



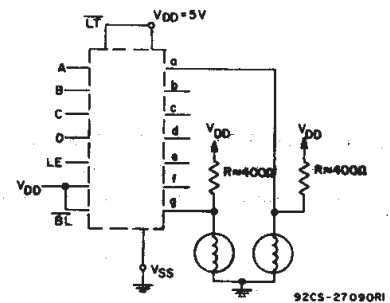
Duty Cycle = 100%
 $I_{SEG} = I_{DIODE\ AVG.} = 20\text{ mA at Luminous Intensity/Segment} = 250\text{ microcandles}$
 $R = \frac{V_{OH} - V_{DF}}{I_{SEG}}$

Fig. 15 - Driving common-cathode 7-segment LED displays (example Hewlet-Packard 5082-7740).

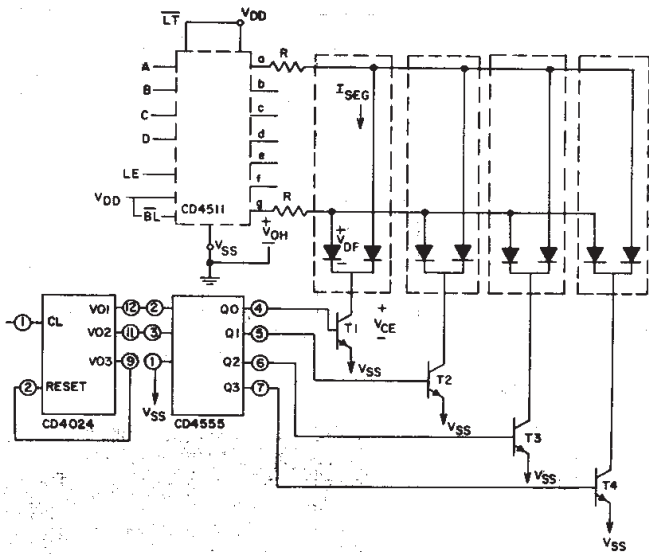


92CS-2709IR
 A medium-brightness intensity display can be obtained with low-voltage fluorescent displays such as the Tung-Sol Digivac S/G** Series.

**Trademark Tung-Sol Division Wagner Electric Co.
 Fig. 16 - Driving low-voltage fluorescent displays.



92CS-2709OR
2 of 7 Segments Shown Connected
 Resistors R from V_{DD} to each 7-segment driver output are chosen to keep all Numitron segments slightly on and warm.
 Fig. 17 - Driving incandescent displays (RCA Numitron DR2000 series displays).

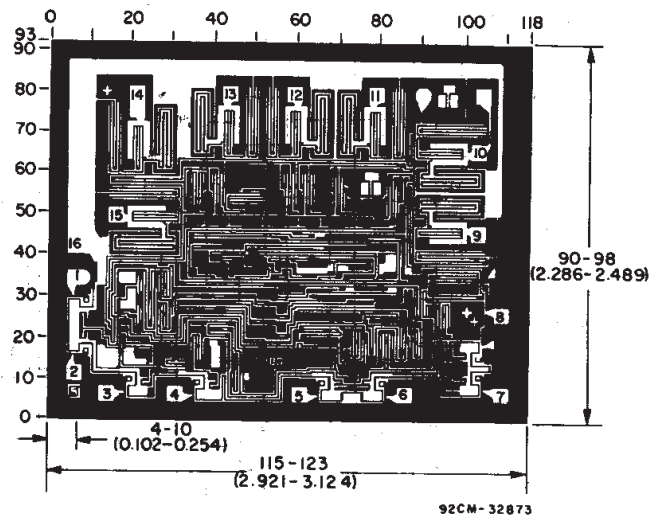


Multiplexing Scheme Showing 2 of 7 Segments Connected 92CM-27087RI
 Transistors T₁-T₄ (RCA-2N3053 or 2N2102) have I_C Max. rating > 7x I_{SEG}

Duty Cycle = 25%
 $I_{SEG} = (I_{DIODE\ AVG.}) \times 4$
 $R = \frac{(V_{OH} - V_{DF} - V_{CE})}{I_{SEG}}$

All unused inputs on CD4555 are connected to V_{DD} or V_{SS}.

Fig. 18 - Multiplexing with common-cathode 7-segment LED displays (example Hewlet-Packard 5082-7404 4 character display or 4 discrete Monosanto Man 3 displays).



Dimensions and pad layout for CD4511B chip.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).

3
 COMMERCIAL CMOS
 HIGH VOLTAGE ICs

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.